

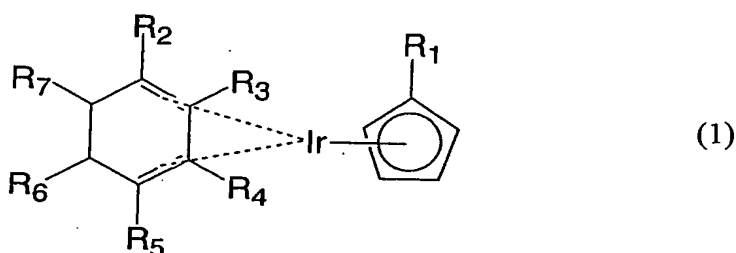
[Designation of Document] Specification

[Title of the Invention]

Novel organometallic iridium compound

[Claim]

[Claim 1] An organometallic iridium compound represented by the following general formula (1):



wherein R₁, R₂, R₃, R₄, R₅, R₆, and R₇ are the same or different and each represents hydrogen, a halogen, a lower acyl group, a lower alkoxy group, a lower alkoxycarbonyl group, or a lower alkyl group, provided that the case where all of R₁, R₂, R₃, R₄, R₅, R₆, and R₇ represent hydrogen is excluded.

[Detailed Description of the Invention]

[0001]

[Technical Field that the Invention Belongs]

The present invention relates to an organometallic compound that can be a material for producing an iridium-containing thin film on a surface of a substrate.

[0002]

[Prior Art]

In recent years, in memory cells, for the sake of making it possible to realize higher integration and higher density, ferroelectric materials having a large relative dielectric constant are being eagerly investigated. Specifically, Ta₂O₅, BST ((Ba,